

## isc N-Channel MOSFET Transistor

## IRLZ44N, IIRLZ44N

## • FEATURES

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 22m\Omega$
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## • DESCRIPTION

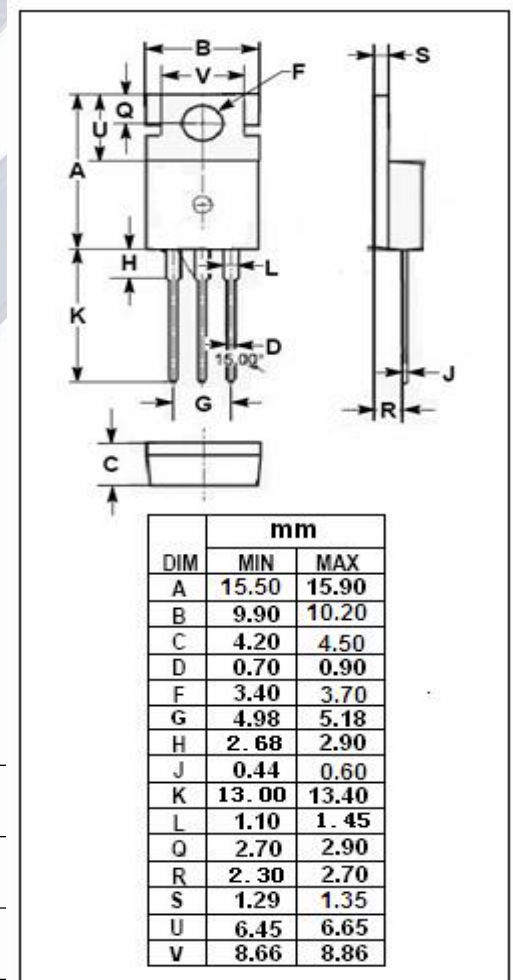
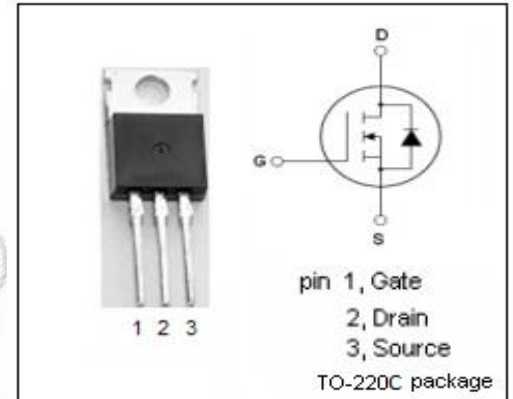
- reliable device for use in a wide variety of applications

• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DS}$	Drain-Source Voltage	55	V
$V_{GS}$	Gate-Source Voltage	$\pm 16$	V
$I_D$	Drain Current-Continuous	47	A
$I_{DM}$	Drain Current-Single Pulsed	160	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	110	W
$T_j$	Max. Operating Junction Temperature	175	$^\circ C$
$T_{stg}$	Storage Temperature	-55~175	$^\circ C$

## • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	1.4	$^\circ C/W$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^\circ C/W$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$BV_{DS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ ; $I_D=250\mu A$	55			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ ; $I_D=250\mu A$	1.0		2.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V$ ; $I_D=25A$			22	$m\Omega$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 16V$			$\pm 0.1$	$\mu A$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=55V$ ; $V_{GS}=0V$			25	$\mu A$
$V_{SD}$	Diode forward voltage	$I_S=25A$ , $V_{GS}=0V$			1.3	V